

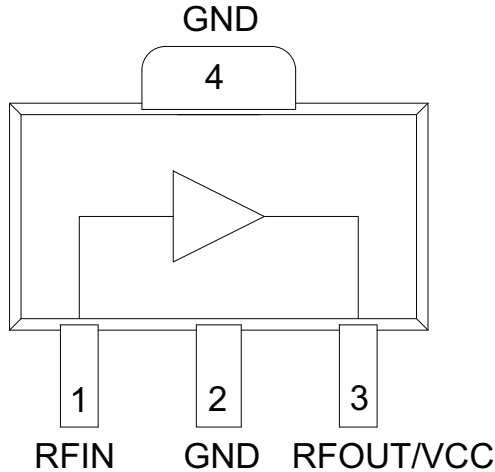


Features

- -60dBc ACPR at 16dBm WCDMA
- 0.5W Output Power (P1dB)
- Excellent Linearity to DC Power Ratio
- NF=3.0dB at 880MHz
- Single-Supply 5V Operation
- Class 1C (100V) HBM ESD

Applications

- GaAs Pre-Driver for Base Station Amplifiers
- PA Stage for Commercial Wireless Infrastructure
- 2nd or 3rd Stage LNAs
- Class AB Operation for GSM, DCS, PCS, UMTS, WiMAX, LTE Transceiver Applications



Functional Block Diagram

Product Description

The RFPA2189 is a single-stage GaAs HBT power amplifier specifically designed for Wireless Infrastructure applications. It offers ultra-linear operation at a comparably low DC power making it ideal for next generation radios requiring high efficiency. Its external matching allows for use across various radio platforms within 400MHz to 2700MHz. The RFPA2189 offers low noise figure making it an excellent solution for 2nd and 3rd stage LNAs.

Ordering Information

| | |
|-----------------|---|
| RFPA2189SR | 7" Reel with 100 pieces |
| RFPA2189SQ | Sample bag with 25 pieces |
| RFPA2189TR7 | 7" Reel with 2500 pieces |
| RFPA2189PCK-410 | 869MHz to 894MHz PCBA with 5-piece sample bag |
| RFPA2189PCK-411 | 2110MHz to 2170MHz PCBA with 5-piece sample bag |

Optimum Technology Matching® Applied

- | | | | |
|--|--------------------------------------|-------------------------------------|------------------------------------|
| <input checked="" type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS | <input type="checkbox"/> Si CMOS | <input type="checkbox"/> BIFET HBT |
| <input type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si BJT | |

Absolute Maximum Ratings

| Parameter | Rating | Unit |
|---------------------------------------|-------------|------|
| Supply Voltage (V_{CC}) | 6.0 | V |
| DC Supply Current (I_C) | 380 | mA |
| CW Input Power, 50Ω output | 20 | dBm |
| Output Load VSWR at P3dB | 5:1 | |
| Operating Junction Temperature | 160 | °C |
| Operating Temperature Range (T_L) | -40 to +85 | °C |
| Storage Temperature | -55 to +150 | °C |
| ESD Rating – Human Body Model (HBM) | Class 1C | |
| Moisture Sensitivity Level | MSL2 | |

Notes:

- The maximum ratings must all be met simultaneously.
- $P_{DISS} = P_{DC} + P_{RFIN} - P_{RFOUT}$
- $T_J = T_L + P_{DISS} * R_{TH}$



Caution! ESD sensitive device.

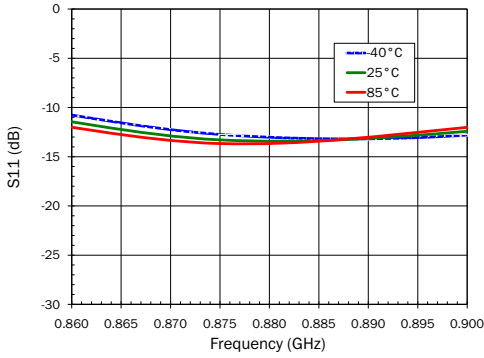
Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

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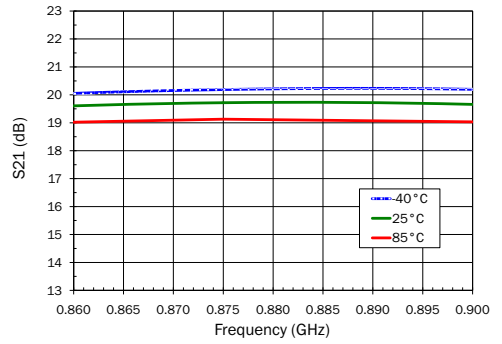
| Parameter | Specification | | | Unit | Condition |
|------------------------------------|---------------|------|------|------|--|
| | Min. | Typ. | Max. | | |
| 869 MHz to 894 MHz | | | | | |
| | | | | | $V_{CC}=5.0V, I_{CQ}=155mA$ |
| Frequency | 869 | 880 | 894 | MHz | EVB tuned for optimum ACPR |
| Input Power (Pin) | | | 13 | dBm | Max recommended continuous input power, $V_{CC}<5.25V$, Load VSWR < 2:1 |
| Gain (S21) | | 19.5 | | dB | |
| OIP3 | | 43 | | dBm | 15 dBm/tone, tone spacing=1 MHz |
| P1dB | | 27.5 | | dBm | EVB tuned for linear operation |
| Input Return Loss (S11) | | 13 | | dB | |
| Output Return Loss (S22) | | 13 | | dB | |
| Noise Figure | | 2.8 | | dB | |
| WCDMA Channel Power at -55dBc ACPR | | 17 | | dBm | 3GPP 3.5, Test Model 1, 64 DPCH |
| UMTS 2100MHz | | | | | |
| | | | | | $V_{CC}=5.0V, I_{CQ}=155mA$ |
| Frequency | 2110 | 2140 | 2170 | MHz | EVB tuned for optimum ACPR |
| Input Power (Pin) | | | 18 | dBm | Max recommended continuous input power, $V_{CC}<5.25V$, Load VSWR < 2:1 |
| Gain (S21) | | 14.5 | | dB | |
| OIP3 | | 42.5 | | dBm | 15 dBm/tone, tone spacing=1 MHz |
| P1dB | | 27 | | dBm | EVB tuned for linear operation |
| Input Return Loss (S11) | | 13 | | dB | |
| Output Return Loss (S22) | | 13 | | dB | |
| Noise Figure | | 2.8 | | dB | |
| WCDMA Channel Power at -55dBc ACPR | | 16.8 | | dBm | 3GPP 3.5, Test Model 1, 64 DPCH |
| Power Supply | | | | | |
| Operating Current (Quiescent) | | 155 | | mA | At $V_{CC}=5.0V$ |
| Operating Voltage (V_{CC}) | | 5.0 | 5.25 | V | Max recommended collector voltage for continuous operation |
| Thermal Resistance (R_{TH}) | | 58 | | C/W | At $V_{CC}=5.0V$ |

Typical Performance – 869MHz to 894MHz Application Circuit

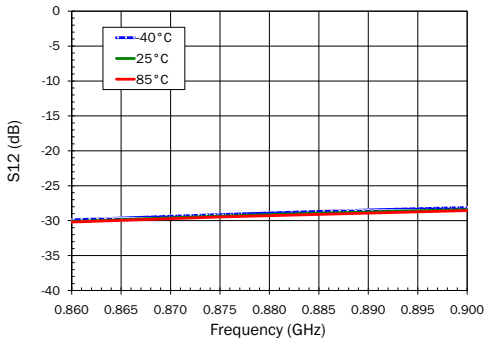
S11 versus Frequency



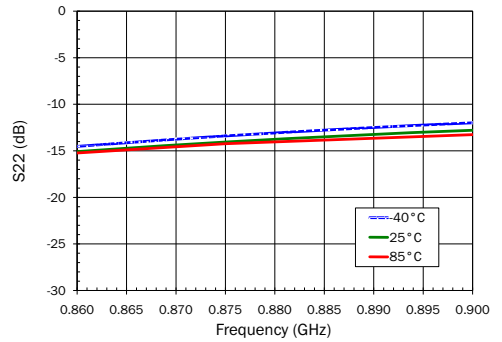
S21 versus Frequency



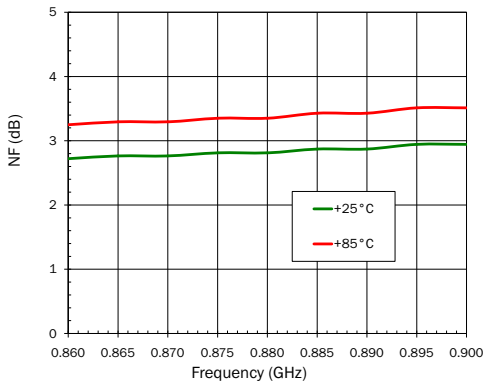
S12 versus Frequency



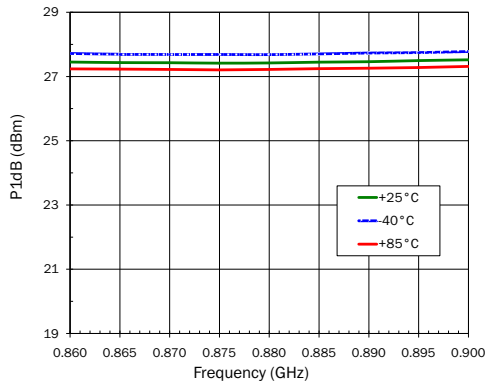
S22 versus Frequency



NF versus Frequency

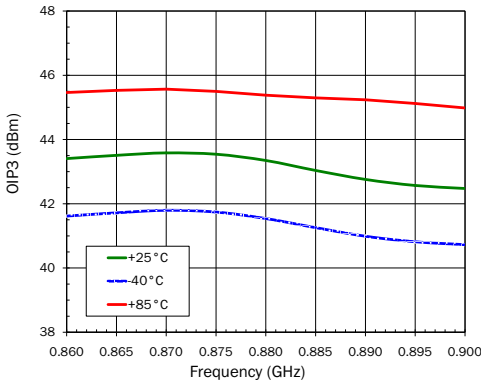


P1dB versus Frequency

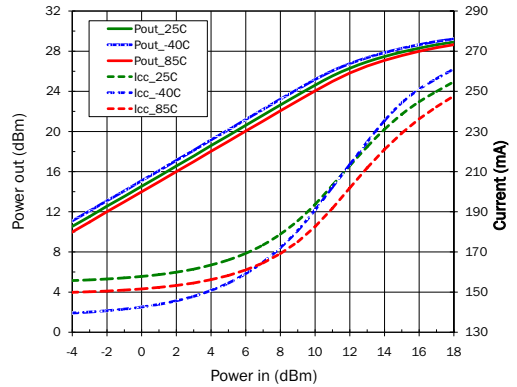


Typical Performance – 869MHz to 894MHz Application Circuit

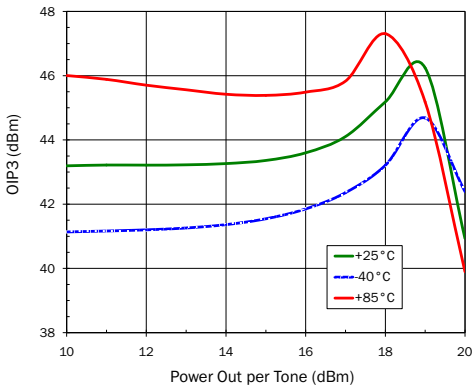
OIP3 versus Frequency (15dBm tones)



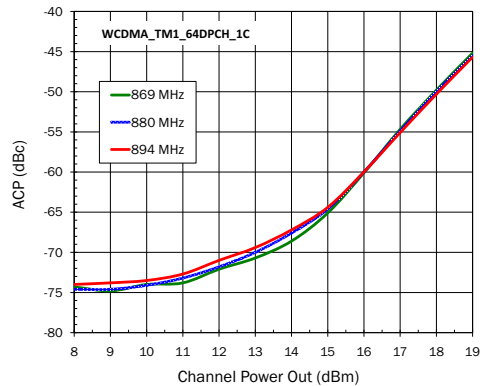
Pout & Current versus Pin @ 880MHz



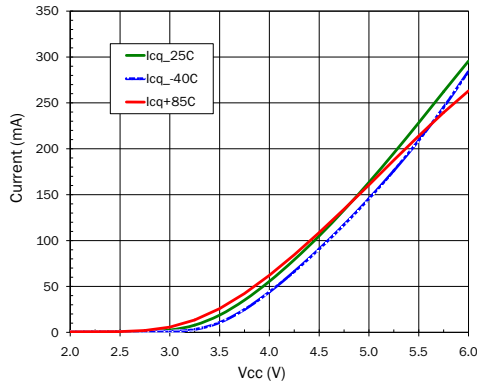
OIP3 versus Power Out (880 MHz)



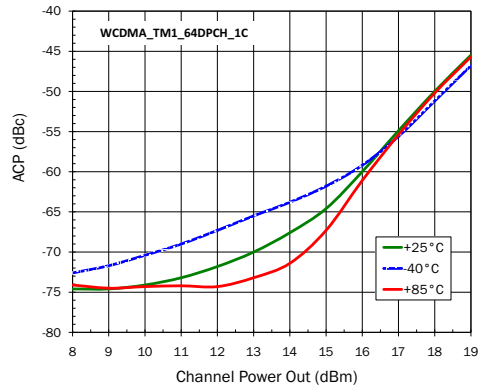
ACP versus Power Out (25°C)



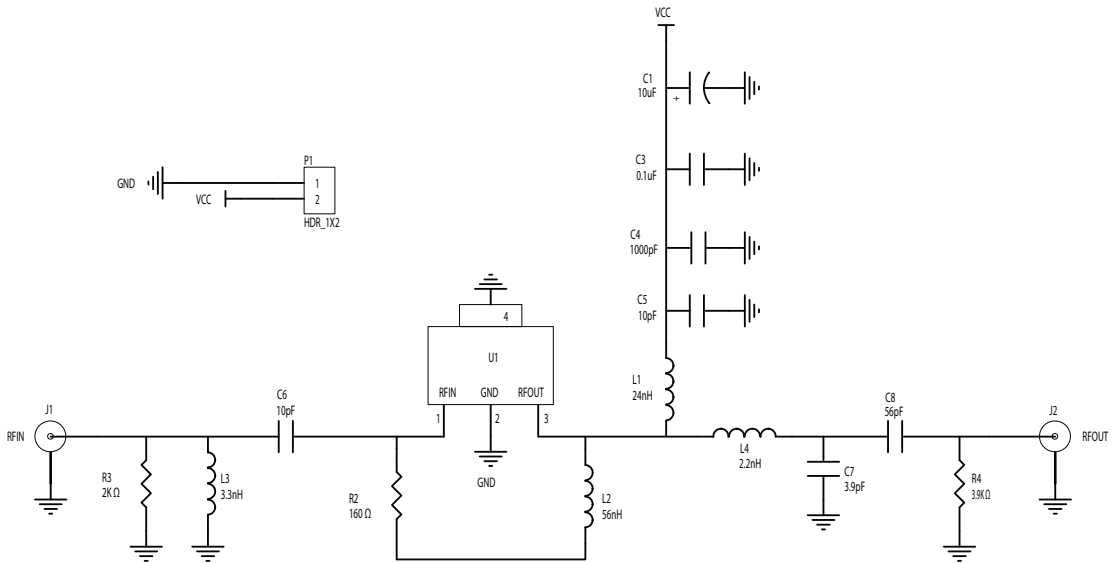
Current vs. Voltage



ACP versus Power Out (880MHz)



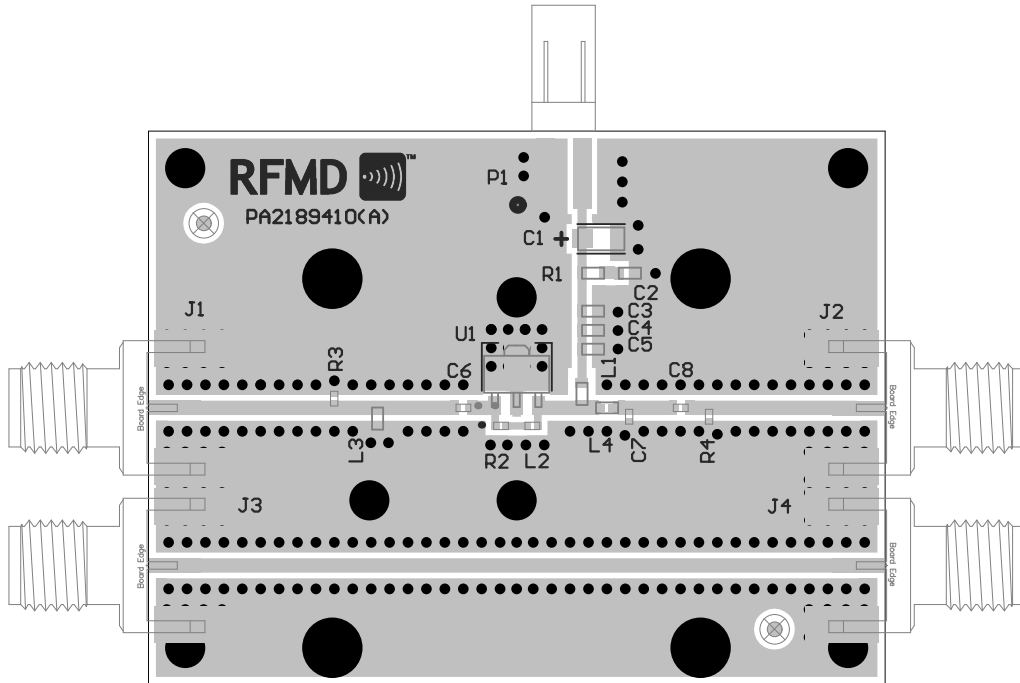
Evaluation Board Schematic 869MHz to 894MHz Application Circuit



Evaluation Board Bill of Materials (BOM) 869MHz to 894MHz Application Circuit

| Description | Reference Designator | Manufacturer | Manufacturer's P/N |
|---|----------------------|---------------------|--------------------|
| PCB | | | PA2189410(A) |
| GaAs HBT Power Amplifier | U1 | RFMD | RFPA2189 |
| CAP, 10 uF, 20%, 10V, TANT-A | C1 | Kemet | T491A106M010AT |
| CAP, 1000 pF, 10%, 50V, X7R, 0603 | C4 | Panasonic | ECJ-1VB1H102K |
| CAP, 0.1uF, 10%, 16V, X7R, 0603 | C3 | Murata Electronics | GRM188R71C104KA01D |
| CAP, 10 pF, 5%, 50V, COG, 0603 | C5 | Johanson Technology | 500R14N100JV4 |
| CAP, 10 pF, 5%, 50V, COG, 0402 | C6 | Murata Electronics | GRM1555C1H100JZ01E |
| CAP, 3.9 pF, +/-0.25 pF, 50V, COG, 0402 | C7 | Murata Electronics | GRM1555C1H3R9CZ01E |
| CAP, 56 pF, 5%, 50V, COG, 0402 | C8 | Murata Electronics | GRM1555C1H560JZ01D |
| CONN, SMA, END LNCH, MINI, FLT, 0.068" | J1, J2 | Emerson Networks | 142-0741-851 |
| IND, 24 nH, 5%, W/W, 0603 | L1 | Coilcraft, Inc. | 0603HC-24NXJLW |
| IND, 56 nH, 5%, M/L, 0402 | L2 | TOKO | LL1005-FHL56NJ |
| IND, 3.3 nH, +/- 0.3 nH, M/L, 0603 | L3 | TOKO | LL1608-FSL3N3S |
| IND, 2.2 nH, +/-0.3 nH, M/L, 0603 | L4 | TOKO | LL1608-FSL2N2S |
| CONN, HDR, ST, PLRZD, 2-PIN, 0.100" | P1 | ITW Pancon | MPSS100-2-C |
| RES, 160Ω, 5%, 1/16W, 0402 | R2 | Kamaya, Inc | RMC1/16S-161JTH |
| RES, 2K, 5%, 1/16W, 0402 | R3 | Panasonic | ERJ-2GEJ202 |
| RES, 3.9K, 5%, 1/16W, 0402 | R4 | Panasonic | ERJ-2GEJ392 |
| DNP | R1, C2, J3, J4 | | |

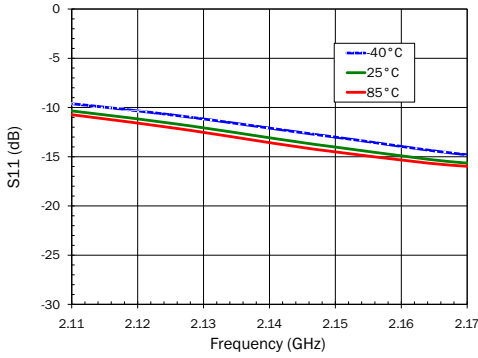
Evaluation Board Assembly Drawing 869 MHz to 894 MHz Application Circuit



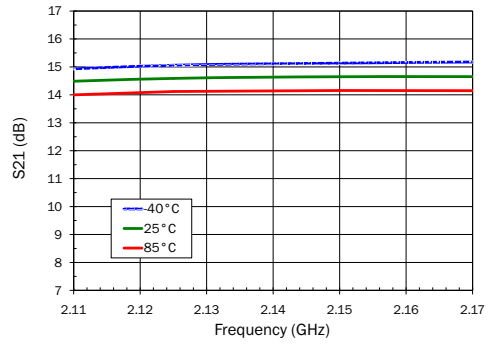
(Refer to Schematic and BOM for specific component requirements, some items in the EVB drawing are DNP)

Typical Performance – 2110MHz to 2170MHz Application Circuit

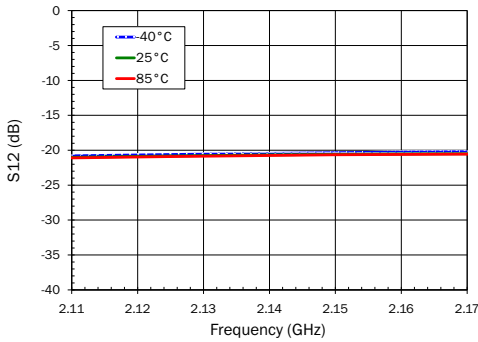
S11 versus Frequency



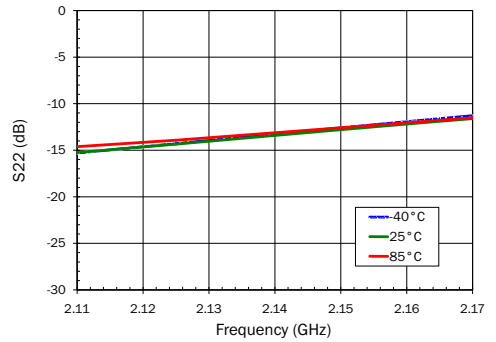
S21 versus Frequency



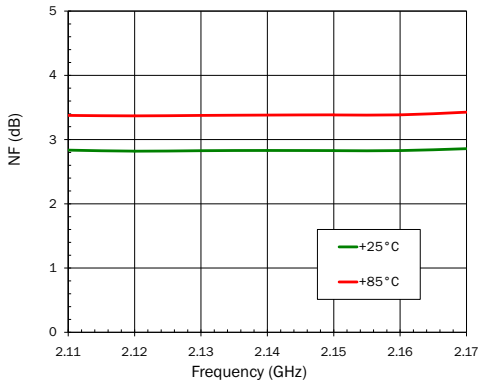
S12 versus Frequency



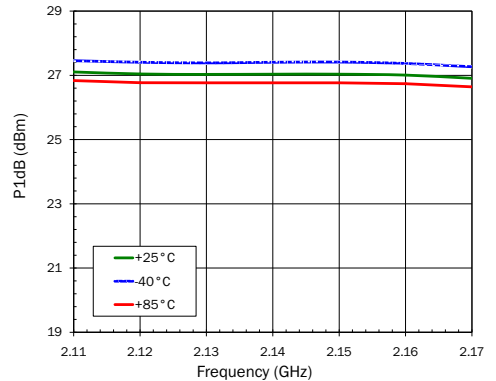
S22 versus Frequency



NF versus Frequency

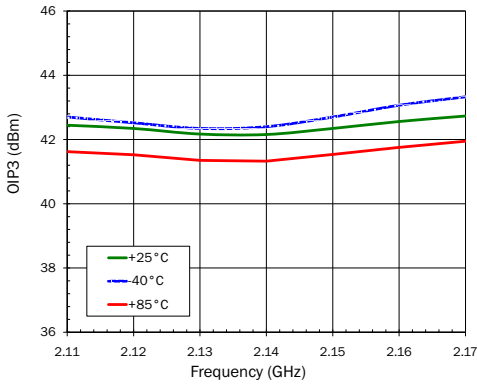


P1dB versus Frequency

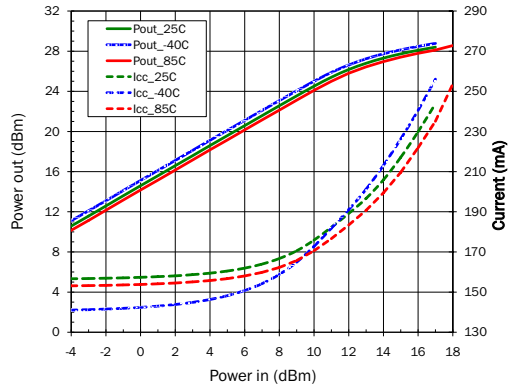


Typical Performance – 2110MHz to 2170MHz Application Circuit

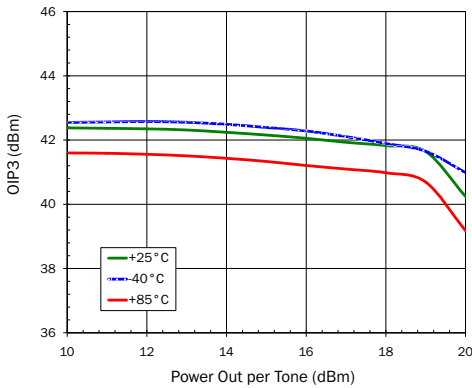
OIP3 versus Frequency (15dBm tones)



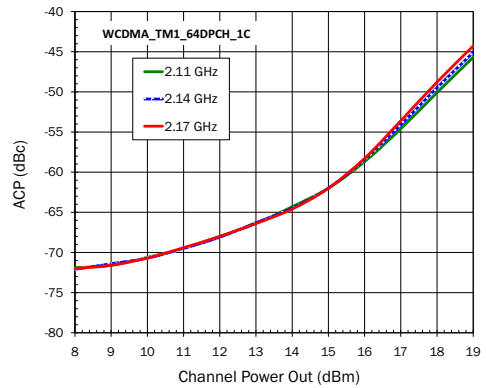
Pout & Current versus Pin @ 2140MHz



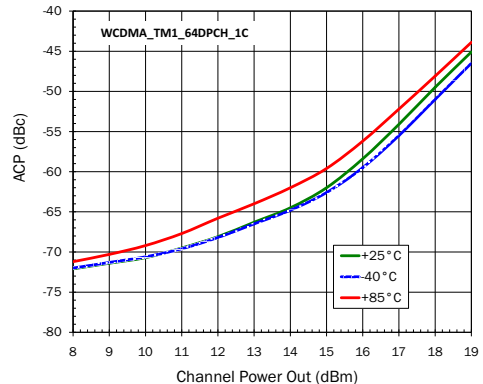
OIP3 versus Power Out (2140 MHz)



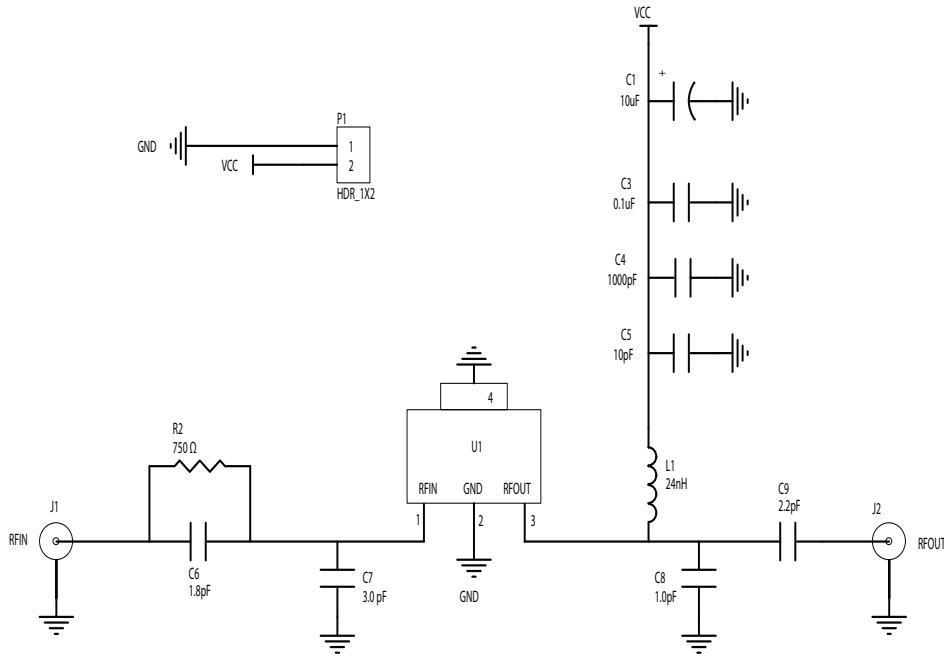
ACP versus Power Out (25°C)



ACP versus Power Out (2140 MHz)



Evaluation Board Schematic 2110MHz to 2170MHz Application Circuit

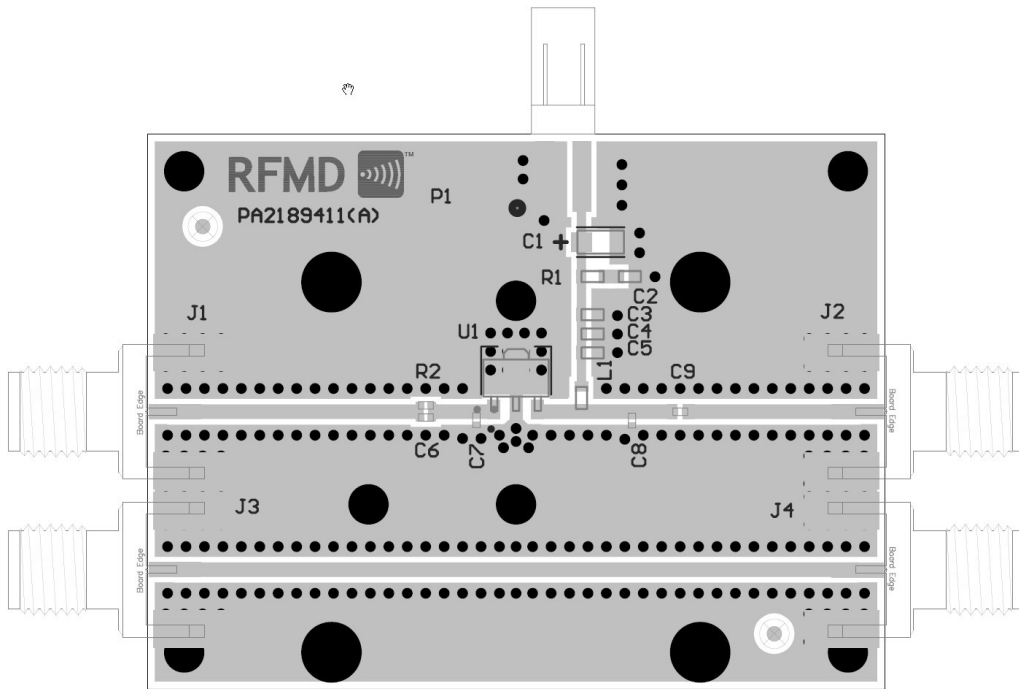


Evaluation Board Bill of Materials (BOM)

2110MHz to 2170MHz Application Circuit

| Description | Reference Designator | Manufacturer | Manufacturer's P/N |
|---|----------------------|---------------------|--------------------|
| PCB | | | PA2189411(A) |
| GaAs HBT Power Amplifier | U1 | RFMD | RFPA2189 |
| CAP, 10 uF, 20%, 10V, TANT-A | C1 | Kemet | T491A106M010AT |
| CAP, 1000 pF, 10%, 50V, X7R, 0603 | C4 | Panasonic | ECJ-1VB1H102K |
| CAP, 0.1 uF, 10%, 16V, X7R, 0603 | C3 | Murata Electronics | GRM188R71C104KA01D |
| CAP, 10 pF, 5%, 50V, COG, 0603 | C5 | Johanson Technology | 500R14N100JV4 |
| CAP, 1.8 pF, +/-0.1 pF, 50V, COG, 0402 | C6 | Murata Electronics | GRM1555C1H1R8BZ01E |
| CAP, 3 pF, +/-0.1 pF, 50V, COG, 0402 | C7 | Murata Electronics | GRM1555C1H3R0BZ01E |
| CAP, 1 pF, +/-0.1 pF, 50V, HI-Q, 0402 | C8 | Johanson Technology | 500R07S1R0BV4TD |
| CAP, 2.2 pF, +/-0.1 pF, 50V, HI-Q, 0402 | C9 | Johanson Technology | 500R07S2R2BV4TD |
| CONN, SMA, END LNCH, MINI, FLT, 0.068" | J1, J2 | Emerson Networks | 142-0741-851 |
| IND, 24 nH, 5%, W/W, 0603 | L1 | Coilcraft, Inc. | 0603HC-24NXJLW |
| CONN, HDR, ST, PLRZD, 2-PIN, 0.100" | P1 | ITW Pancon | MPSS100-2-C |
| RES, 750Ω, 1%, 1/16W, 0402 | R2 | Panasonic | ERJ-2RK7500X |
| DNP | R1, C2, J3, J4 | | |

Evaluation Board Assembly Drawing 2110MHz to 2170MHz Application Circuit

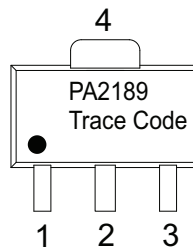


(Refer to Schematic and BOM for specific component requirements, some items in the EVB drawing are DNP)

Pin Names and Description

| Pin | Function | Description |
|-----|------------|---|
| 1 | RF IN | RF Input. External DC Block is Required. |
| 2 | GND | DC and RF Ground |
| 3 | RF OUT/VCC | RF Output, Device Collector |
| 4 | GND | DC and RF Ground. Must be soldered to EVB ground plane over a bed of vias for thermal and RF performance. |

Package Marking



Trace Code to be assigned by the assembly SubCon.

Package Drawing

Dimensions in millimeters [inches]

Refer to drawing posted at www.rfmd.com for tolerances.

